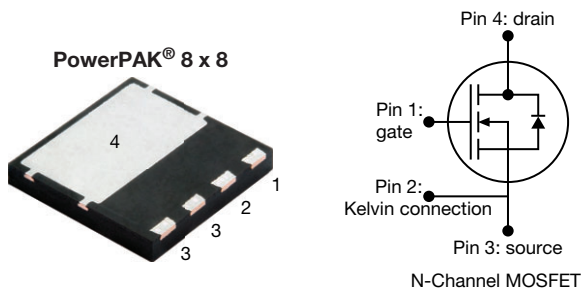


## EF Series Power MOSFET With Fast Body Diode



### FEATURES

- 4<sup>th</sup> generation E series technology
- Low figure of merit (FOM)  $R_{DS(on)} \times Q_g$
- Low effective capacitance ( $C_{o(er)}$ )
- Reduced switching and conduction losses
- Avalanche energy rated (UIS)
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
**GREEN**  
(5-2008)

### APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
  - High-intensity discharge (HID)
  - Fluorescent ballast lighting
- Industrial
  - Welding
  - Induction heating
  - Motor drives
  - Battery chargers
  - Solar (PV inverters)

### PRODUCT SUMMARY

$V_{DS}$ (V) at $T_J$ max.	650	
$R_{DS(on)}$ typ. ( $\Omega$ ) at 25 °C	$V_{GS} = 10$ V	0.075
$Q_g$ max. (nC)	63	
$Q_{gs}$ (nC)	17	
$Q_{gd}$ (nC)	9	
Configuration	Single	

### ORDERING INFORMATION

Package	PowerPAK 8 x 8
Lead (Pb)-free and halogen-free	SiHH085N60EF-T1GE3

### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-source voltage			$V_{DS}$	600	V
Gate-source voltage			$V_{GS}$	$\pm 30$	
Continuous drain current ( $T_J = 150\text{ }^{\circ}\text{C}$ )	$V_{GS}$ at 10 V	$T_C = 25\text{ }^{\circ}\text{C}$	$I_D$	30	A
		$T_C = 100\text{ }^{\circ}\text{C}$		19	
Pulsed drain current <sup>a</sup>			$I_{DM}$	75	
Linear derating factor				1.47	W/ $^{\circ}\text{C}$
Single pulse avalanche energy <sup>b</sup>			$E_{AS}$	173	mJ
Maximum power dissipation			$P_D$	184	W
Operating junction and storage temperature range			$T_J, T_{stg}$	-55 to +150	$^{\circ}\text{C}$
Drain-source voltage slope		$T_J = 125\text{ }^{\circ}\text{C}$	dv/dt	100	V/ns
Reverse diode dv/dt <sup>d</sup>				50	


#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature
- $V_{DD} = 120$  V, starting  $T_J = 25$  °C,  $L = 28.2$  mH,  $R_g = 25$   $\Omega$ ,  $I_{AS} = 3.5$  A
- 1.6 mm from case
- $I_{SD} \leq I_D$ , di/dt = 100 A/ $\mu$ s, starting  $T_J = 25$  °C

**THERMAL RESISTANCE RATINGS**

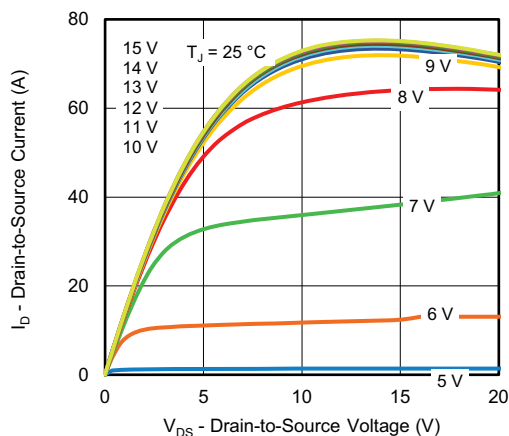
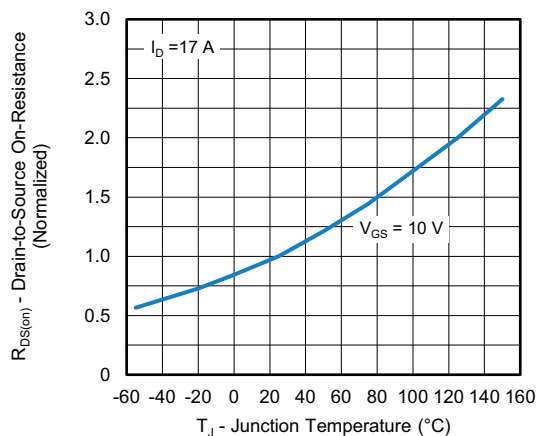
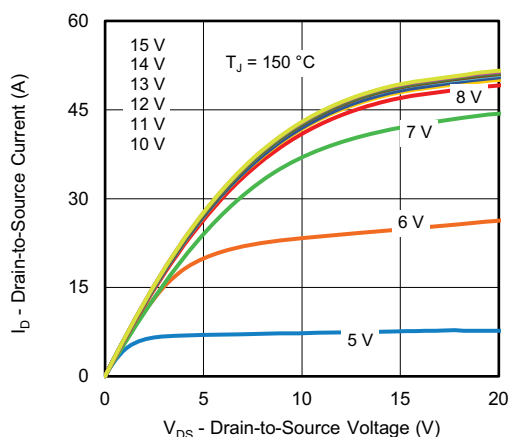
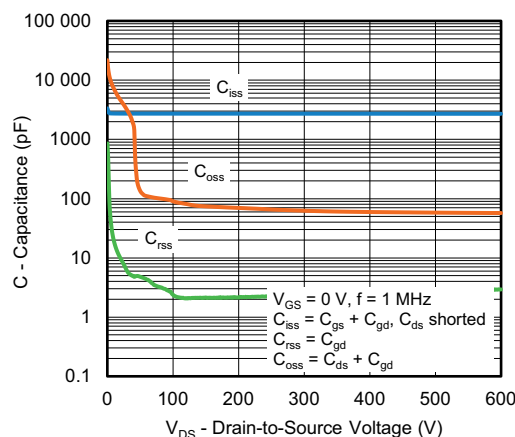
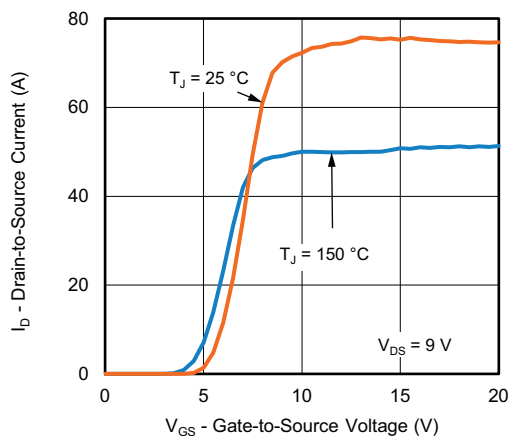
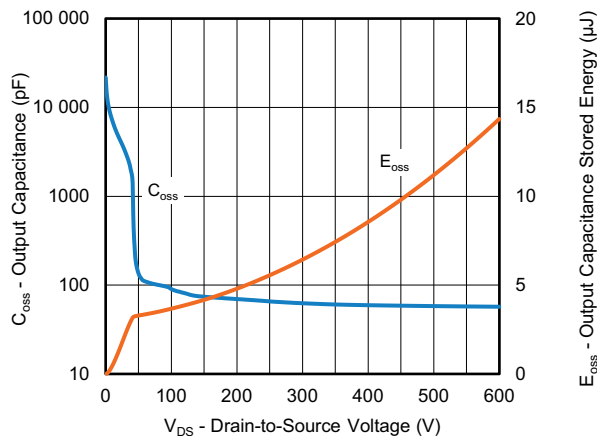
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	$R_{thJA}$	39	51	°C/W
Maximum junction-to-case (drain)	$R_{thJC}$	0.51	0.68	

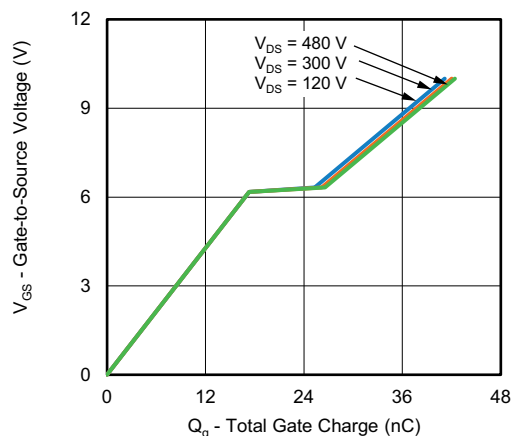
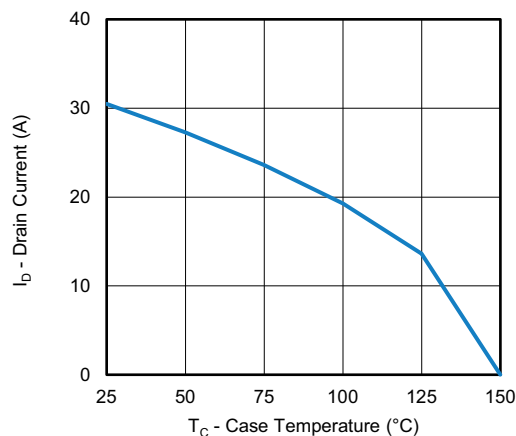
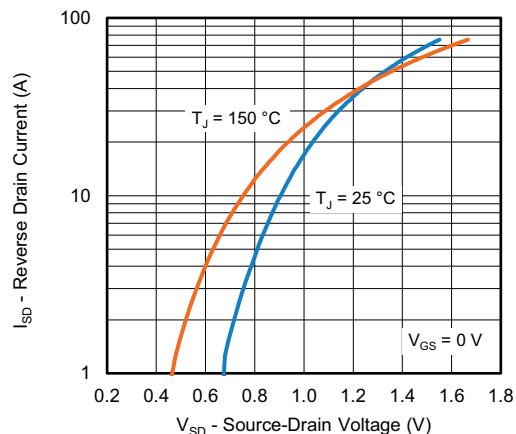
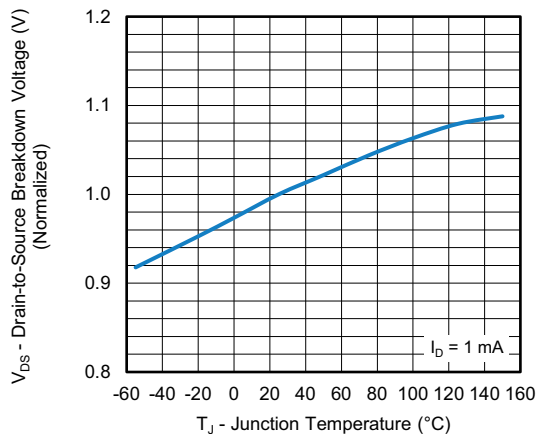
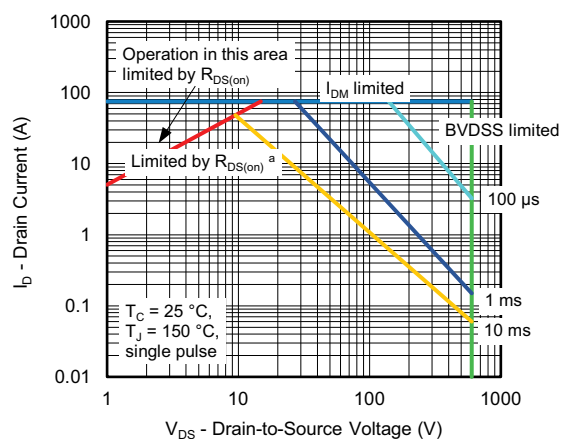
**SPECIFICATIONS** ( $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA		600	-	-	V
V <sub>DS</sub> temperature coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	Reference to 25 °C, I <sub>D</sub> = 1 mA		-	0.56	-	V/°C
Gate-source threshold voltage (N)	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA		3.0	-	5.0	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>GS</sub> = ± 20 V		-	-	± 100	nA
		V <sub>GS</sub> = ± 30 V		-	-	± 1	μA
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 480 V, V <sub>GS</sub> = 0 V		-	-	1	μA
		V <sub>DS</sub> = 480 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C		-	-	2	mA
Drain-source on-state resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 17 A	-	0.075	0.085	Ω
Forward transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 17 A		-	16	-	S
Dynamic							
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 100 V, f = 100 KHz		-	2733	-	pF
Output capacitance	C <sub>oss</sub>			-	100	-	
Reverse transfer capacitance	C <sub>rss</sub>			-	3	-	
Effective output capacitance, energy related <sup>a</sup>	C <sub>o(er)</sub>	V <sub>DS</sub> = 0 V to 400 V, V <sub>GS</sub> = 0 V		-	107	-	pF
Effective output capacitance, time related <sup>b</sup>	C <sub>o(tr)</sub>			-	645	-	
Total gate charge	Q <sub>g</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 17 A, V <sub>DS</sub> = 480 V	-	42	63	nC
Gate-source charge	Q <sub>gs</sub>			-	17	-	
Gate-drain charge	Q <sub>gd</sub>			-	9	-	
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = 480 V, I <sub>D</sub> = 17 A, V <sub>GS</sub> = 10 V, R <sub>g</sub> = 9.1 Ω		-	32	64	ns
Rise time	t <sub>r</sub>			-	75	113	
Turn-off delay time	t <sub>d(off)</sub>			-	48	96	
Fall time	t <sub>f</sub>			-	53	80	
Gate input resistance	R <sub>g</sub>	f = 1 MHz		0.3	0.7	1.4	Ω
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	I <sub>S</sub>	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	30	A
Pulsed diode forward current	I <sub>SM</sub>			-	-	75	
Diode forward voltage	V <sub>SD</sub>	T <sub>J</sub> = 25 °C, I <sub>S</sub> = 17 A, V <sub>GS</sub> = 0 V		-	-	1.2	V
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C, I <sub>F</sub> = I <sub>S</sub> = 17 A, di/dt = 100 A/μs, V <sub>R</sub> = 400 V		-	109	218	ns
Reverse recovery charge	Q <sub>rr</sub>			-	0.6	1.2	μC
Reverse recovery current	I <sub>RRM</sub>			-	11	-	A

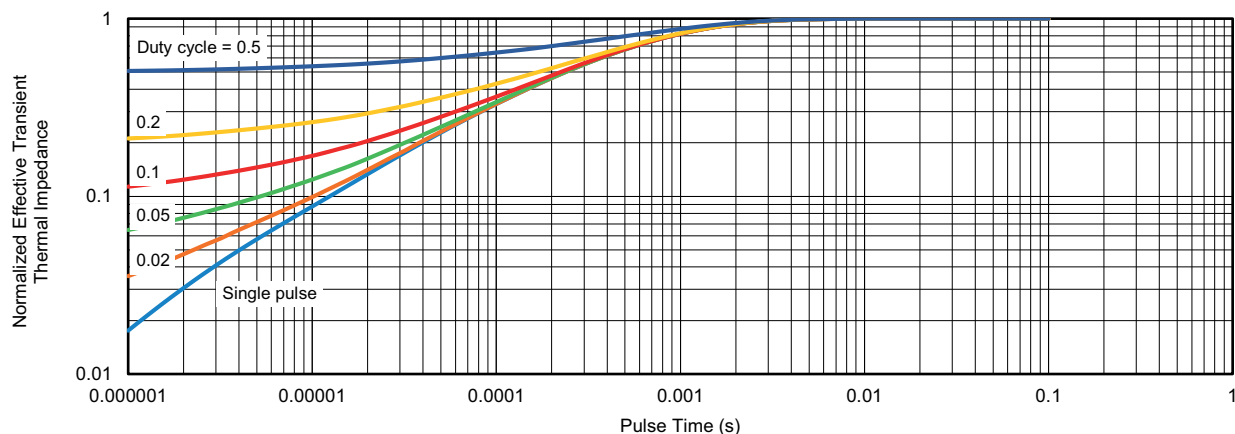
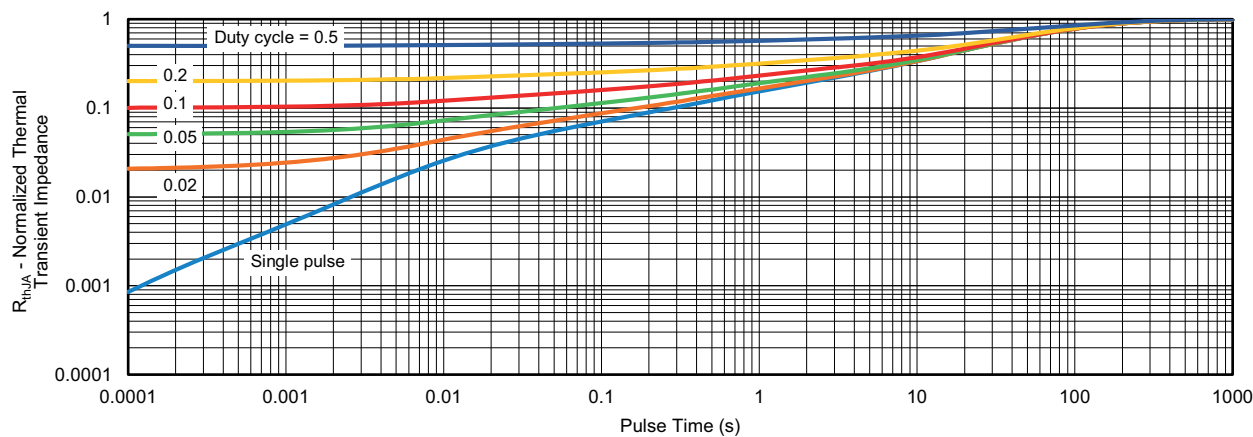
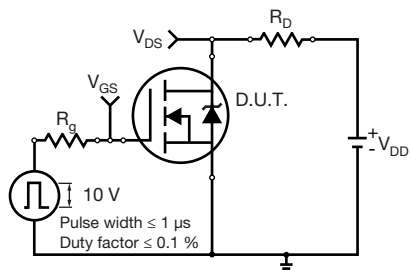
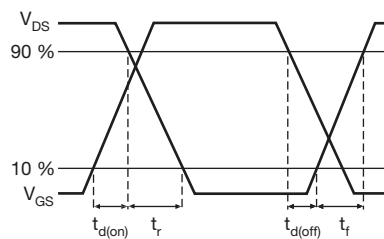
**Notes**

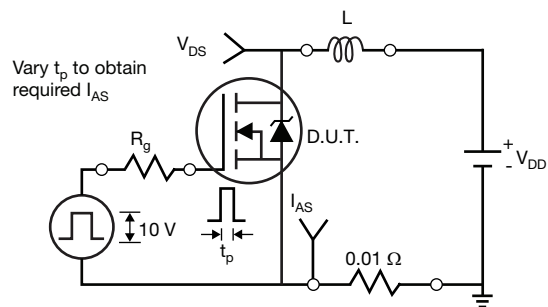
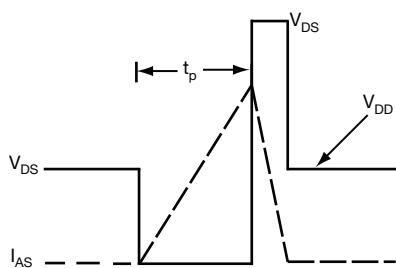
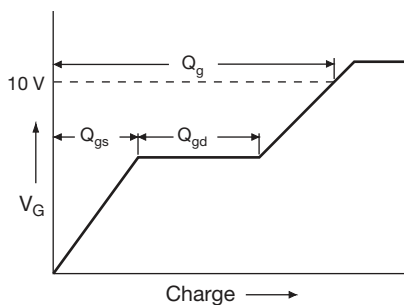
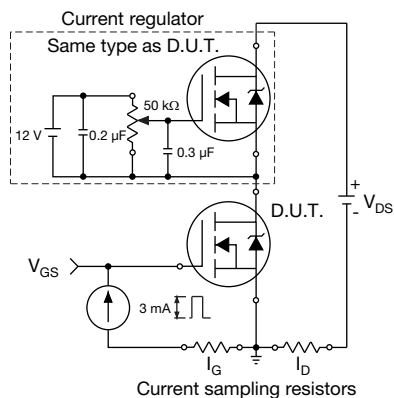
- a.  $C_{oss(er)}$  is a fixed capacitance that gives the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 V to 400 V  
b.  $C_{oss(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 V to 400 V

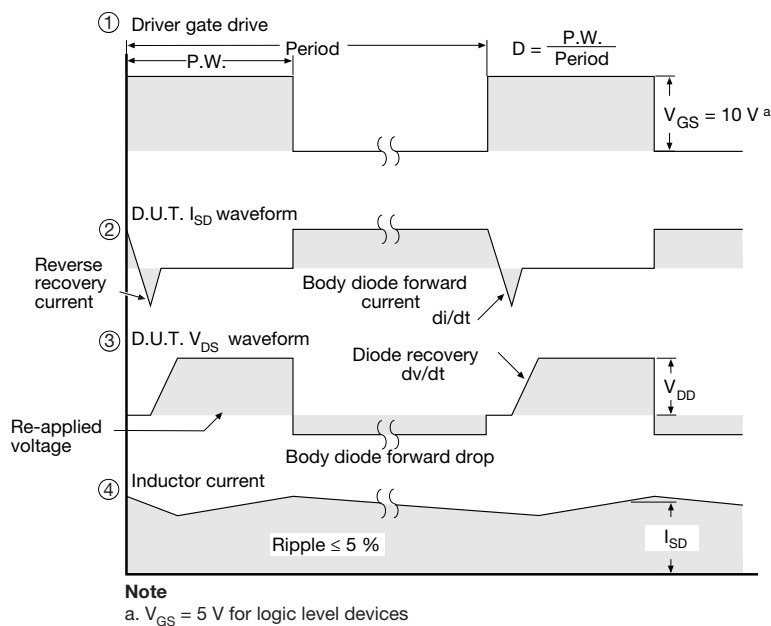
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Fig. 1 - Typical Output Characteristics**

**Fig. 4 - Normalized On-Resistance vs. Temperature**

**Fig. 2 - Typical Output Characteristics**

**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**

**Fig. 3 - Typical Transfer Characteristics**

**Fig. 6 -  $C_{oss}$  and  $E_{oss}$  vs.  $V_{DS}$**


**Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage**

**Fig. 10 - Maximum Drain Current vs. Case Temperature**

**Fig. 8 - Typical Source-Drain Diode Forward Voltage**

**Fig. 11 - Temperature vs. Drain-to-Source Voltage**

**Fig. 9 - Maximum Safe Operating Area**
**Note**

a.  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified


**Fig. 12 - Normalized Transient Thermal Impedance, Junction-to-Case**

**Fig. 13 - Normalized Transient Thermal Impedance, Junction-to-Ambient**

**Fig. 14 - Switching Time Test Circuit**

**Fig. 15 - Switching Time Waveforms**


**Fig. 16 - Unclamped Inductive Test Circuit**

**Fig. 17 - Unclamped Inductive Waveforms**

**Fig. 18 - Basic Gate Charge Waveform**

**Fig. 19 - Gate Charge Test Circuit**



**Fig. 20 - For N-Channel**

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## PowerPAK® 8 x 8 Case Outline



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.95	1.00	1.05	0.037	0.039	0.041
A1	0.00	-	0.05	0.000	-	0.002
A2	020 ref.			0.008 ref.		
b	0.95	1.00	1.05	0.037	0.039	0.041
D	7.90	8.00	8.10	0.311	0.315	0.319
D2	7.10	7.20	7.30	0.280	0.283	0.287
D3	0.40 BSC			0.016 BSC		
e	2.00 BSC			0.079 BSC		
E	7.90	8.00	8.10	0.311	0.315	0.319
E2	4.30	4.35	4.40	0.169	0.171	0.173
E3	0.40 BSC			0.016 BSC		
K	2.75 BSC			0.108 BSC		
L	0.45	0.50	0.55	0.018	0.020	0.022
N <sup>(3)</sup>	8			8		

### Notes

- (1) Use millimeters as the primary measurement
- (2) Dimensioning and tolerances conform to ASME Y14.5 M - 1994
- (3) N is the number of terminals
- (4) The pin 1 identifier must be existed on the top surface of the package by using indentation mark or other feature of package body
- (5) Exact shape and size of this feature is optional

ECN: E20-0518-Rev. B, 28-Sep-2020  
DWG: 6041





## Recommended Minimum PADs for PowerPAK® 8 mm x 8 mm



Dimensions in millimeters



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